MBR30HxxCT, MBRF30HxxCT, MBRB30HxxCT

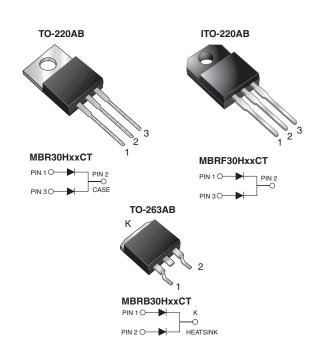
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Vishay General Semiconductor

RoHS

Dual Common Cathode Schottky Rectifier

High Barrier Technology for Improved High Temperature Performance



PRIMARY CHARACTERISTICS					
I _{F(AV)}	2 x 15 A				
V _{RRM}	35 V, 45 V, 50 V, 60 V				
I _{FSM}	150 A				
V _F	0.56 V, 0.59 V				
I _R	80 μΑ, 60 μΑ				
T _J max.	175 °C				
Package	TO-220AB, ITO-220AB, TO-263AB				
Diode variations	Dual Common Cathode				

FEATURES

Power pack



- · Lower power losses, high efficiency
- Low forward voltage drop
- · Low leakage current
- High forward surge capability
- High frequency operation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C (for TO-263AB package)
- Solder bath temperature 275 °C maximum, 10 s, per JESD 22-B106 (for TO-220AB and ITO-220AB package)
- AEC-Q101 qualified
- Material categorization: For definitions of compliance please see <u>www.vishav.com/doc?99912</u>

TYPICAL APPLICATIONS

For use in low voltage, high frequency rectifier of switching mode power supplies, freewheeling diodes, DC/DC converters, or polarity protection application.

MECHANICAL DATA

Case: TO-220AB, ITO-220AB, TO-263AB

Molding compound meets UL 94 V-0 flammability rating Base P/N-E3 - RoHS-compliant, commercial grade Base P/NHE3 - RoHS-compliant, AEC-Q101 qualified

Terminals: Matte tin plated leads, solderable per

J-STD-002 and JESD 22-B102

E3 suffix meets JESD 201 class 1A whisker test, HE3 suffix meets JESD 201 class 2 whisker test

Polarity: As marked

Mounting Torque: 10 in-lbs maximum

MAXIMUM RATINGS (T _A = 25 °C unless otherwise noted)							
PARAMETER	SYMBOL	MBR30H35CT	MBR30H45CT	MBR30H50CT	MBR30H60CT	UNIT	
Maximum repetitive peak reverse voltage	V_{RRM}	35	45	50	60	V	
Working peak reverse voltage	V_{RWM}	35	45	50	60	V	
Maximum DC blocking voltage	V_{DC}	35	45	50	60	V	
Maximum average forward rectified total device	1	30				Α	
current (fig. 1) per diode	I _{F(AV)}	15					
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode	I _{FSM}	150			Α		
Peak repetitive reverse surge current per diode at t_p = 2 μ s, 1 kHz	I _{RRM}	1.0 0.5			Α		
Peak non-repetitive reverse energy (8/20 µs waveform)	E _{RSM}	25 20		mJ			



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MAXIMUM RATINGS (T _A = 25 °C unless otherwise noted)							
PARAMETER	SYMBOL	MBR30H35CT	MBR30H45CT	MBR30H50CT	MBR30H60CT	UNIT	
Non-repetitive avalanche energy per diode at 25 $^{\circ}$ C, I_{AS} = 4 A, L = 10 mH	E _{AS}	80				mJ	
Electrostatic discharge capacitor voltage human body model: C = 100 pF, R = 1.5 k Ω	V _C	25				kV	
Voltage rate of change (rated V _R)	dV/dt	10 000			V/µs		
Operating junction and storage temperature range	T _J , T _{STG}	- 65 to + 175				°C	
Isolation voltage (ITO-220AB only) from terminal to heatsink t = 1 min	V _{AC}	1500				V	

ELECTRICAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)								
PARAMETER	TEST CONDITIONS		SYMBOL	MBR30H35CT MBR30H45CT		MBR30H50CT MBR30H60CT		UNIT
Maximum instantaneous forward voltage per diode ⁽¹⁾	I _F = 15 A	T _C = 25 °C		-	0.62	=	0.68	V
	I _F = 15 A	T _C = 125 °C	V_{F}	0.49	0.56	0.55	0.59	
	$I_F = 30 \text{ A}$	T _C = 25 °C		-	0.73	-	0.83	
	$I_F = 30 \text{ A}$	T _C = 125 °C		0.62	0.67	0.68	0.71	
Maximum reverse current per diode at		$T_J = 25 ^{\circ}C$	I _R	ı	80	ı	60	μΑ
working peak reverse voltage (2)		T _J = 125 °C		5.0	15	4.0	15	mA

Notes

 $^{(1)}$ Pulse test: 300 μs pulse width, 1 % duty cycle

(2) Pulse test: Pulse width ≤ 40 ms

THERMAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)						
PARAMETER SYMBOL MBR MBRF MBRB UNIT						
Typical thermal resistance junction to case per diode	$R_{ hetaJC}$	1.5	4.5	1.5	°C/W	

ORDERING INFORMATION (Example)							
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE		
TO-220AB	MBR30H45CT-E3/45	1.85	45	50/tube	Tube		
ITO-220AB	MBRF30H45CT-E3/45	1.99	45	50/tube	Tube		
TO-263AB	MBRB30H45CT-E3/45	1.35	45	50/tube	Tube		
TO-263AB	MBRB30H45CT-E3/81	1.35	81	800/teel	Tape and reel		
TO-220AB	MBR30H45CTHE3/45 (1)	1.85	45	50/tube	Tube		
ITO-220AB	MBRF30H45CTHE3/45 (1)	1.99	45	50/tube	Tube		
TO-263AB	MBRB30H45CTHE3/45 (1)	1.35	45	50/tube	Tube		
TO-263AB	MBRB30H45CTHE3/81 ⁽¹⁾	1.35	81	800/teel	Tape and reel		

Note

(1) AEC-Q101 qualified

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RATINGS AND CHARACTERISTICS CURVES (T_A = 25 °C unless otherwise noted)

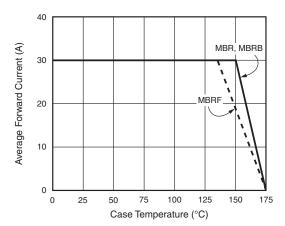


Fig. 1 - Forward Derating Curve

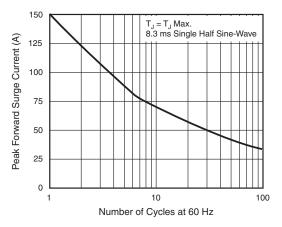


Fig. 2 - Maximum Non-Repetitive Peak Forward Surge Current Per Diode

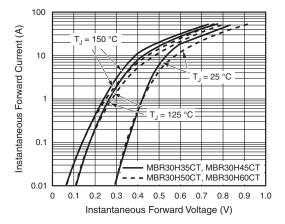


Fig. 3 - Typical Instantaneous Forward Characteristics Per Diode

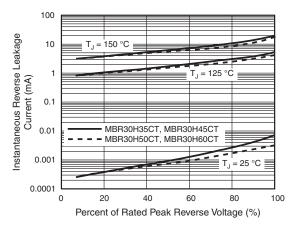


Fig. 4 - Typical Reverse Characteristics Per Diode

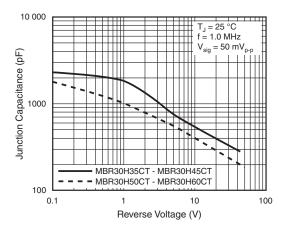


Fig. 5 - Typical Junction Capacitance Per Diode

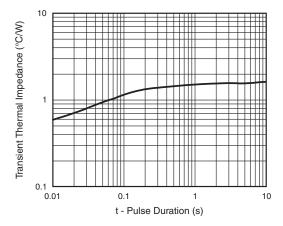


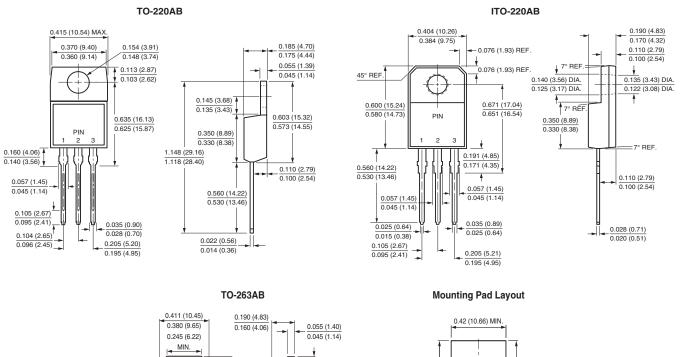
Fig. 6 - Typical Transient Thermal Impedance Per Diode

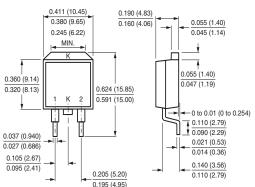


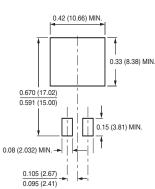
MBR30HxxCT, MBRF30HxxCT, MBRB30HxxCT

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PACKAGE OUTLINE DIMENSIONS in inches (millimeters)









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Revision: 13-Jun-16 1 Document Number: 91000